

PU3210, PU4210, PU4510

加急出货

Package Dimensions

Silicon NPN Epitaxial Planar Type

Power Amplifier, Switching

Complementary Pair with PU3110, PU4110, PU4410

Features

- Low collector-emitter saturation voltage ($V_{CE(sat)}$)
- Good linearity of DC current gain (h_{FE})
- High collector current (I_C)
- PU3210: 3 NPN elements
- PU4210: 4 NPN elements
- PU4510: 2 NPN elements \times 2 (4 elements in total)

Absolute Maximum Ratings ($T_c=25^\circ\text{C}$)

Item	Symbol	Value	Unit
Collector-base voltage	V_{CBO}	-60	V
Collector-emitter voltage	V_{CEO}	-60	V
Emitter-base voltage	V_{EBO}	-6	V
Peak collector current	I_{CP}	-5	A
Collector current	I_C	-3	A
Power dissipation	P_D	15	W
Junction temperature	T_J	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 ~ +150	$^\circ\text{C}$

Electrical Characteristics ($T_c=25^\circ\text{C}$)

Item	Symbol	Condition	min.	typ.	max.	Unit
Collector cutoff current	I_{CES}	$V_{CE} = -60\text{V}, V_{BE} = 0$			-200	μA
	I_{CEO}	$V_{CE} = -30\text{V}, I_B = 0$			-300	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = -6\text{V}, I_C = 0$			-1	mA
Collector-emitter voltage	V_{CEO}	$I_C = -30\text{mA}, I_B = 0$	-60			V
DC current gain	h_{FE1}	$V_{CE} = -4\text{V}, I_C = -1\text{A}$	70		250	
	h_{FE2}	$V_{CE} = -4\text{V}, I_C = -3\text{A}$	10			
Collector-emitter voltage	V_{BE}	$V_{CE} = -4\text{V}, I_C = -3\text{A}$			-1.8	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -3\text{A}, I_B = -0.375\text{A}$			-1.2	V
Transition frequency	f_T	$V_{CE} = -10\text{V}, I_C = -0.5\text{A}, f = 10\text{MHz}$		30		MHz
Turn-on time	t_{on}			0.5		μs
Storage time	t_{stg}	$I_C = -1\text{A}, I_{B1} = -0.1\text{A}, I_{B2} = 0.1\text{A}$		1.2		μs
Fall time	t_f			0.3		μs

Inner Circuit



